

Is Now Part of



# **ON Semiconductor**®

# To learn more about ON Semiconductor, please visit our website at <u>www.onsemi.com</u>

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (\_), the underscore (\_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (\_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at <a href="https://www.onsemi.com">www.onsemi.com</a>. Please email any questions regarding the system integration to <a href="https://www.onsemi.com">Fairchild\_questions@onsemi.com</a>.

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized applications, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an ad experson



SEMICONDUCTOR®

November 2013

## FQNL2N50B **N-Channel QFET® MOSFET**

500 V, 0.35 A, 5.3  $\Omega$ 

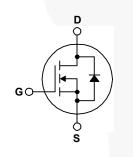
## Description

This N-Channel enhancement mode power MOSFET is • 0.35 A, 500 V,  $R_{DS(on)}$  = 5.3  $\Omega$  (Max.) @ V<sub>GS</sub> = 10 V, produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state  $\cdot$  Low Gate Charge (Typ. 6 nC) resistance, and to provide superior switching performance • Low Crss (Typ. 4 pF) and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

#### Features

- I<sub>D</sub> = 0.175 A





#### Absolute Maximum Ratings T<sub>c</sub> = 25°C unless otherwise noted.

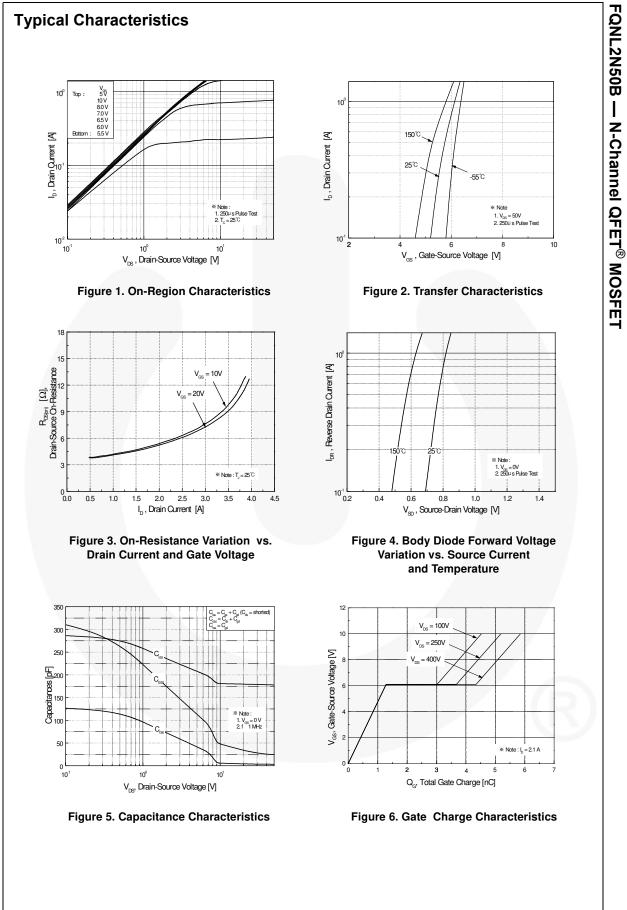
Symbol	Parameter	FQNL2N50BTA	Unit	
V <sub>DSS</sub>	Drain-Source Voltage	500	V	
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°C)		0.35	А
	- Continuous (T <sub>C</sub> = 100°C)		0.22	A
I <sub>DM</sub>	Drain Current - Pulsed	Note 1)	1.4	A
V <sub>GSS</sub>	Gate-Source Voltage		± 30	V
I <sub>AR</sub>	Avalanche Current	Note 1)	0.35	Α
E <sub>AR</sub>	Repetitive Avalanche Energy	Note 1)	0.15	mJ
dv/dt	Peak Diode Recovery dv/dt	Note 2)	4.5	V/ns
PD	Power Dissipation ( $T_C = 25^{\circ}C$ )		1.5	W
	- Derate above 25°C		0.012	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range	-55 to +150	°C	
TL	Maximum lead temperature for soldering,		300	°C
'L	1/8" from case for 5 seconds.	300	U	

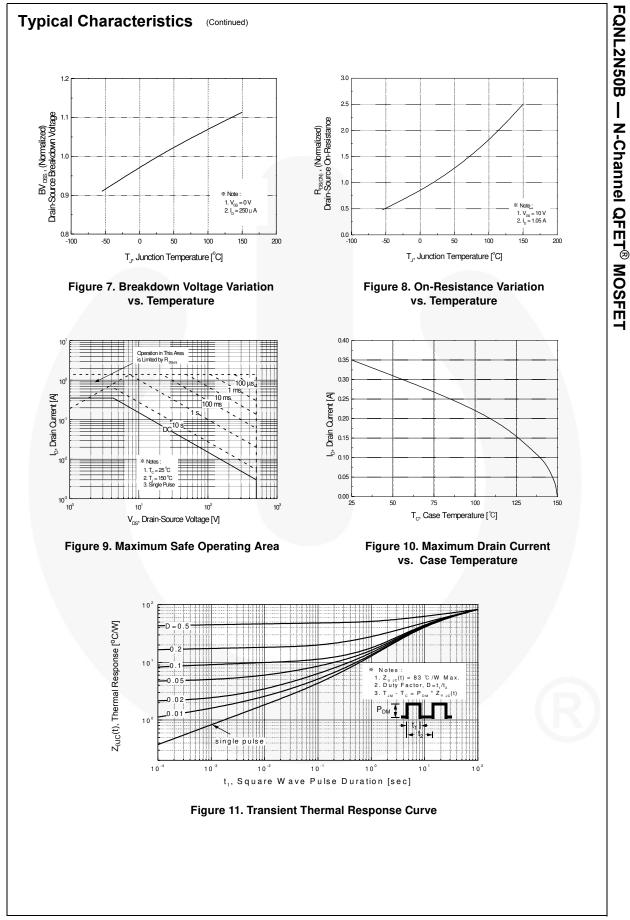
## **Thermal Characteristics**

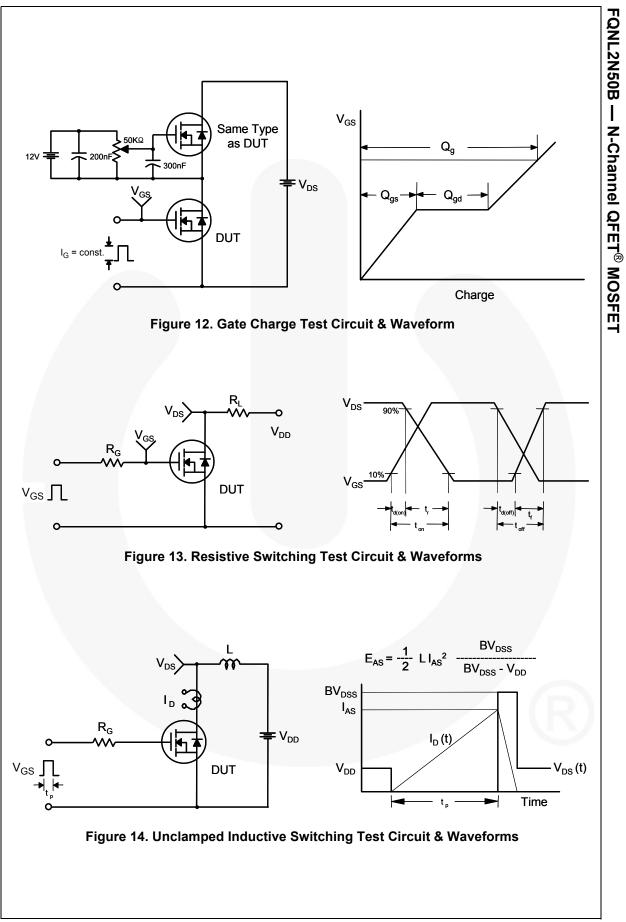
Symbol	Parameter	FQNL2N50BTA Unit			
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction-to-Ambient, Max.	83	°C/W		

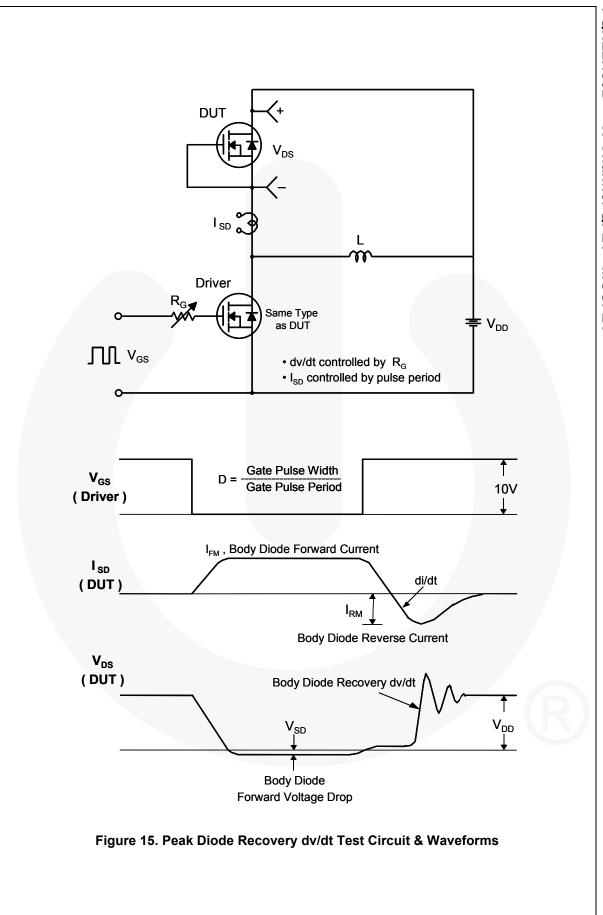
		Pack	kage Packing Method Reel		Size	Tape W	idth	Quantity			
		-92L AMMO			N/	A	N/A		2000 units		
lectri	cal Cha	racteristics	T <sub>C</sub> = 25°C	cunless oth	nerwise noted.						
Symbol		Parameter			Test Con	ditions		Min.	Тур.	Max	. Unit
Off Cha	aracterist	ics									
BV <sub>DSS</sub>	Drain-Sou	rce Breakdown Volta	age	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA			500			V	
ΔBV <sub>DSS</sub> / ΔΤ <sub>J</sub>	Breakdown Voltage Temperature Coefficient			$I_D = 250 \ \mu$ A, Referenced to 25°C				0.48		V/°C	
	Zero Gate Voltage Drain Current		V <sub>DS</sub> = 500 V, V <sub>GS</sub> = 0 V				1	μA			
			ent	$V_{DS} = 400 \text{ V}, \text{ T}_{C} = 125^{\circ}\text{C}$					10	μA	
GSSF	Gate-Body	/ Leakage Current, F	orward	V <sub>GS</sub> = 30 V, V <sub>DS</sub> = 0 V					100	nA	
GSSR	Gate-Body	/ Leakage Current, F	Reverse	V <sub>GS</sub> =	$V_{GS} = -30 \text{ V}, \text{ V}_{DS} = 0 \text{ V}$					-100	nA
On Cha	aracterist	ics									
V <sub>GS(th)</sub>	Gate Threshold Voltage		V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA			2.3	3.0	3.7	V		
00(11)				$V_{DS} = V_{GS}, I_{D} = 250 \text{ mA}$			3.6	4.3	5.0	V	
R <sub>DS(on)</sub>	Static Dra On-Resist			V <sub>GS</sub> = 10 V, I <sub>D</sub> = 0.175 A			4.2	5.3	Ω		
9 <sub>FS</sub>	Forward T	ransconductance		V <sub>DS</sub> =	50 V, I <sub>D</sub> = 0	.175 A			0.72		S
Dynam	ic Charac	teristics									
C <sub>iss</sub>	Input Capa	acitance		V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V,			180	230	pF		
C <sub>oss</sub>	Output Ca	pacitance		f = 1.0					30	40	pF
C <sub>rss</sub>	Reverse T	ransfer Capacitance	•						4	6	pF
Switchi	ing Chara	acteristics									
t <sub>d(on)</sub>	Turn-On D	elay Time		Voo =	250 V, I <sub>D</sub> =	214			6	20	ns
t <sub>r</sub>	Turn-On F	lise Time		$R_G = 2$	_	2.17,			25	60	ns
t <sub>d(off)</sub>	Turn-Off D	elay Time		G -					10	30	ns
t <sub>f</sub>	Turn-Off F	all Time				(	(Note 3)		20	50	ns
Qg	Total Gate	Charge		V <sub>DS</sub> =	400 V, I <sub>D</sub> =	2.1 A,			6.0	8.0	nC
Q <sub>gs</sub>	Gate-Sour	ce Charge		V <sub>GS</sub> = 10 V				1.3		nC	
Q <sub>gd</sub>	Gate-Drai	n Charge				(	(Note 3)		3.0		nC
	Source Di	ode Characteri	stics ar	nd Max	cimum R	atinas					
Is		Continuous Drain-S								0.35	A
I <sub>SM</sub>		Pulsed Drain-Sourc								1.4	A
V <sub>SD</sub>		rce Diode Forward \		$V_{GS} = 0 \text{ V}, \text{ I}_{S} = 0.35 \text{ A}$				/	1.4	V	
t <sub>rr</sub>		Recovery Time	5		0 V, I <sub>S</sub> = 2.				195		ns
Q <sub>rr</sub>		Recovery Charge		00	: = 100 A/με				0.69		μC

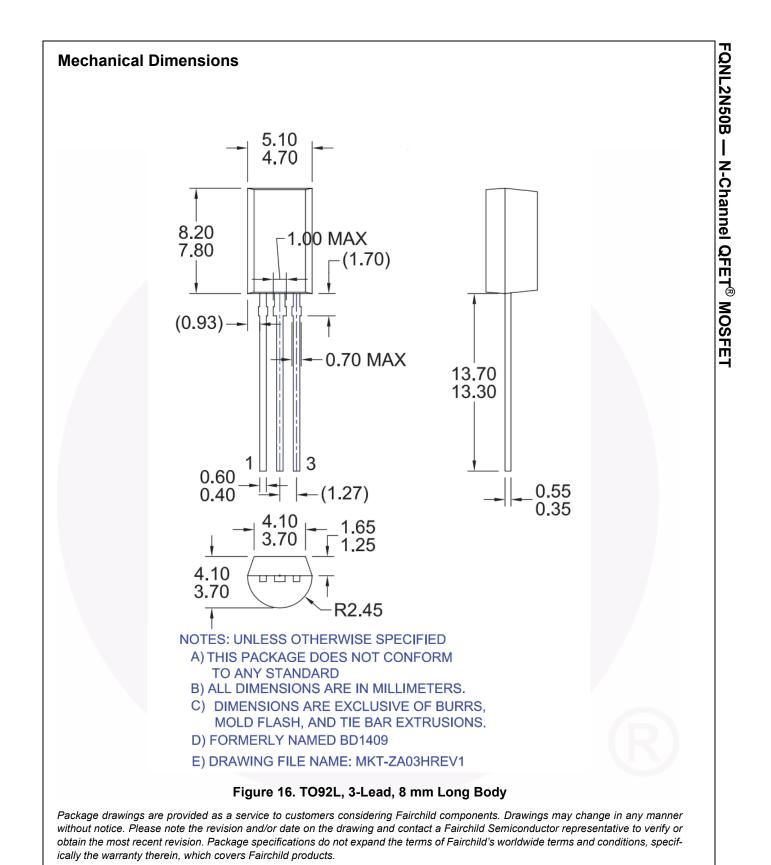
**Notes:** 1. Repetitive rating : pulse-width limited by maximum junction temperature. 2.  $I_{SD} \leq 2.1 \text{ A}$ , di/dt  $\leq 200 \text{ A/}\mu\text{s}$ ,  $V_{DD} \leq BV_{DSS}$ , starting  $T_J = 25^{\circ}\text{C}$ . 3. Essentially independent of operating temperature.











Always visit Fairchild Semiconductor's online packaging area for the most recent package drawings:

http://www.fairchildsemi.com/package/packageDetails.html?id=PN\_TO92-H03



DutuSheet facilitineation		Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.
		Rev. 166

ON Semiconductor and are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at <u>www.onsemi.com/site/pdf/Patent-Marking.pdf</u>. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor has against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death ass

#### PUBLICATION ORDERING INFORMATION

#### LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com N. American Technical Support: 800–282–9855 Toll Free USA/Canada Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Japan Customer Focus Center Phone: 81-3-5817-1050 ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

© Semiconductor Components Industries, LLC